

isc Silicon NPN Power Transistor

2SC2098

DESCRIPTION

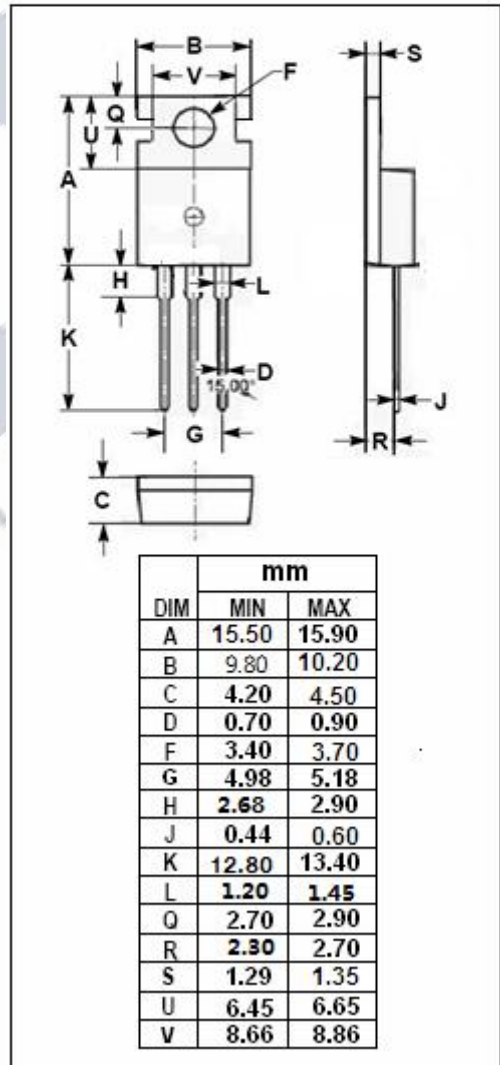
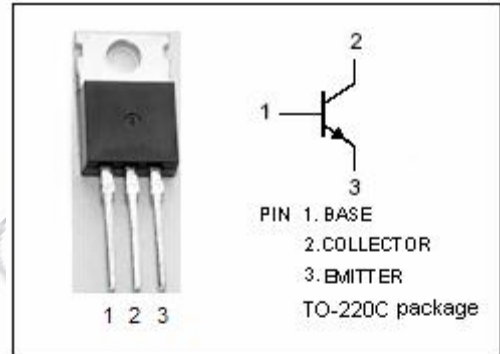
- Silicon NPN epitaxial planar
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- The 2SC2098 is designed for 25-50MHz AF power amplifier applications

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	70	V
V _{CEO}	Collector-Emitter Voltage	70	V
V _{EBO}	Emitter-Base Voltage	4	V
I _c	Collector Current-Continuous	6	A
P _c	Total Power Dissipation @ T _c =25°C	25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



isc Silicon NPN Power Transistor**2SC2098****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=25\text{mA}; I_B=0$	70			V
I_{CBO}	Collector Cutoff Current	$V_{CB}=70\text{V}; I_E=0$			1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			1	mA
h_{FE}	DC Current Gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	20		100	